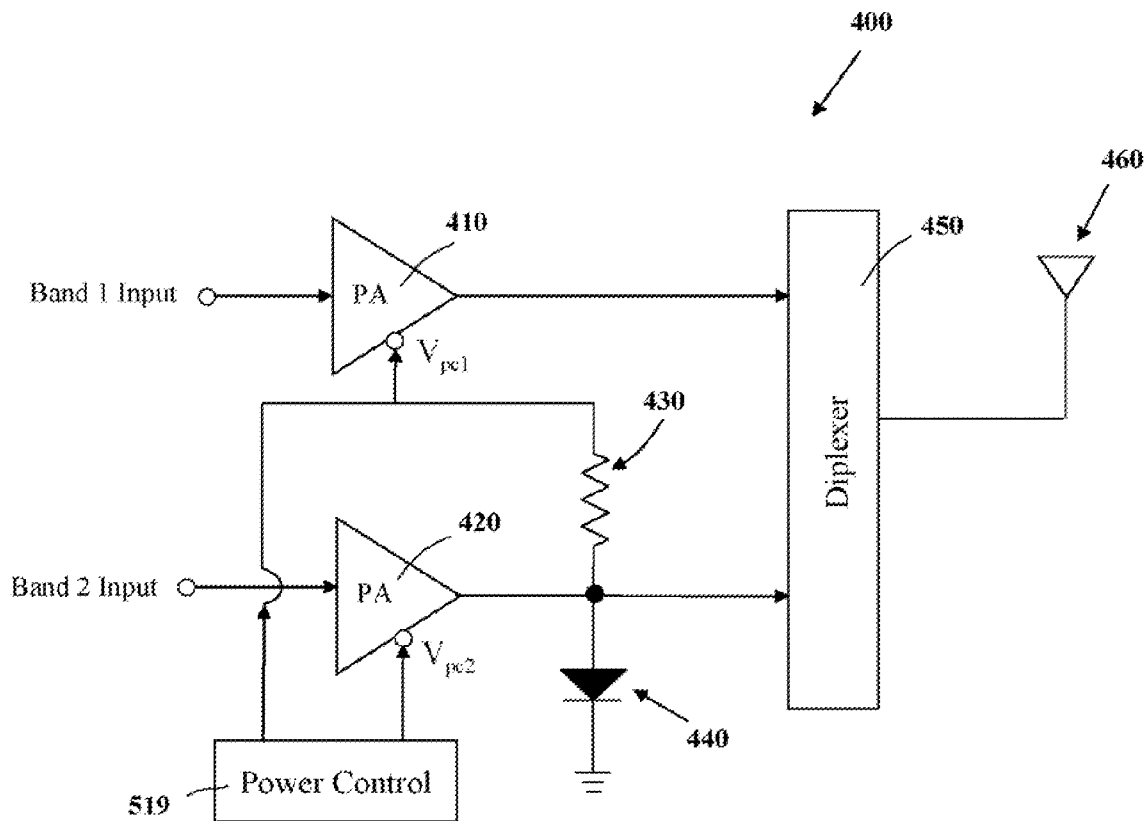




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(19) **United States**(12) **Patent Application Publication**
Ichitsubo(10) **Pub. No.: US 2009/0075608 A1**(43) **Pub. Date: Mar. 19, 2009**(54) **MULTI-BAND AMPLIFIER MODULE WITH
HARMONIC SUPPRESSION****Publication Classification**(51) **Int. Cl.**
H04B 1/04 (2006.01)(52) **U.S. Cl.** **455/127.2**(57) **ABSTRACT**

An amplifier circuit includes a first power amplifier that can produce a first amplified signal in response to a first input signal in a first frequency band, and a second power amplifier that can produce a second amplified signal in response to a second input signal in a second frequency band. A center frequency of the second frequency band is higher than the a center frequency of frequency band A control circuit can turn on or turn off the first power amplifier and configured to turn on or turn off the second power amplifier. A shunting circuit is coupled to an output of the second power amplifier. The shunting circuit can attenuate harmonic signals from the first frequency band under the control of the control circuit.

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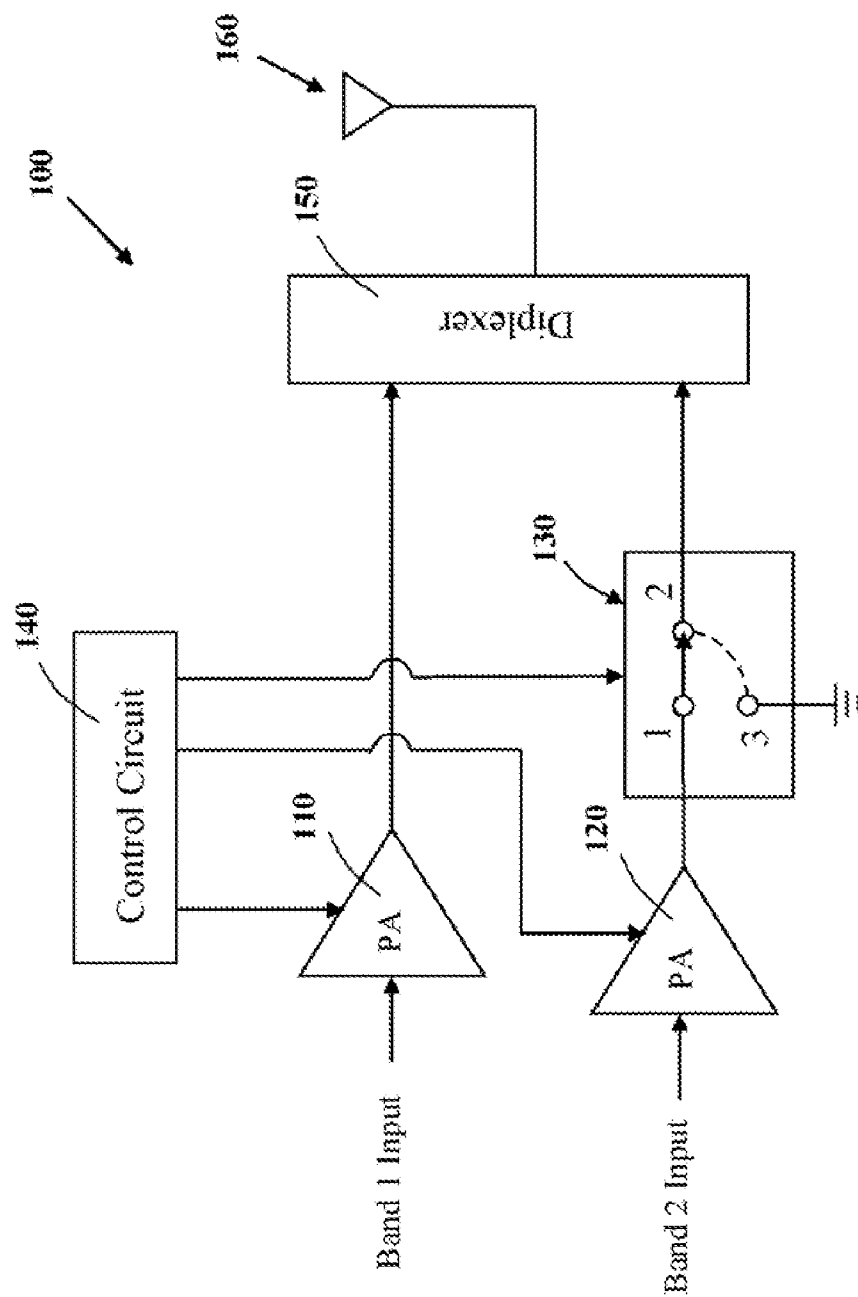


Figure 1

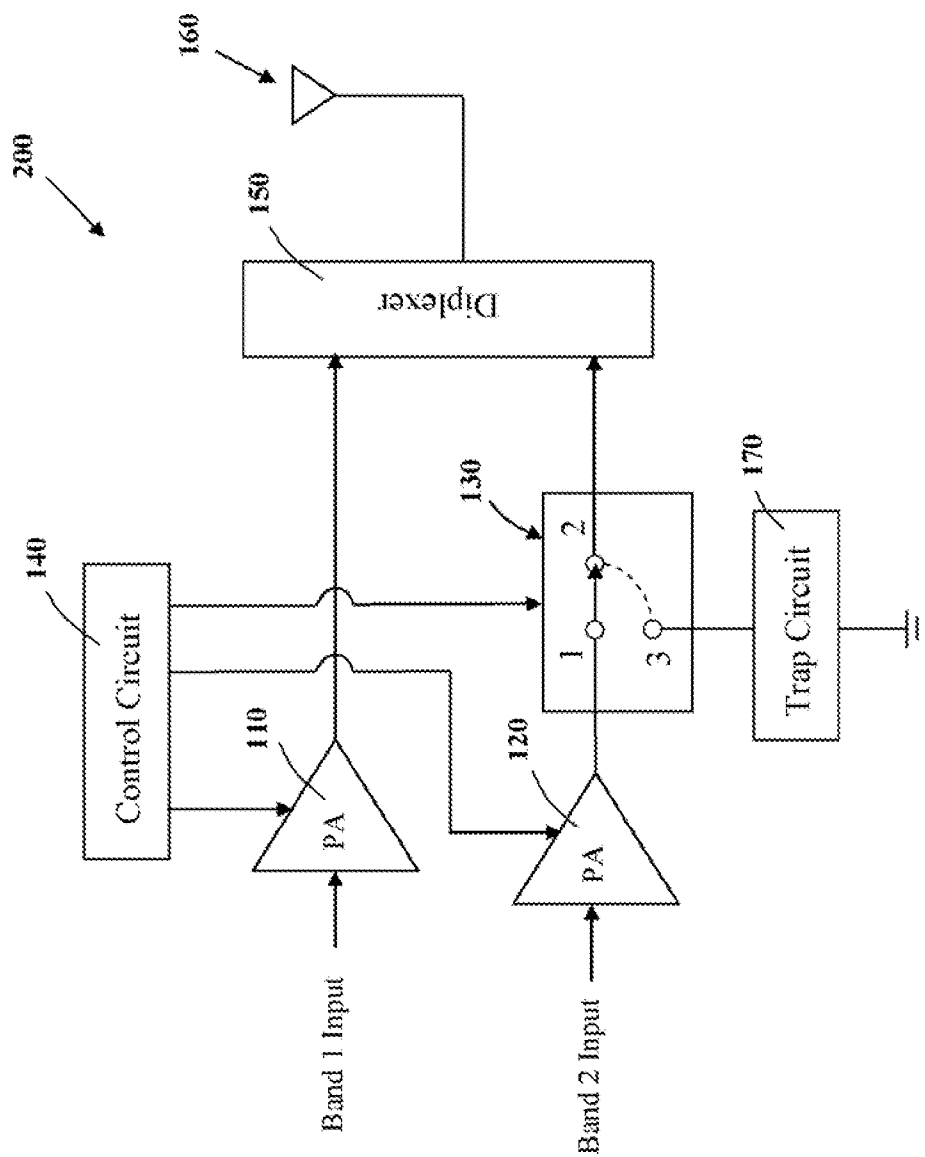


Figure 2

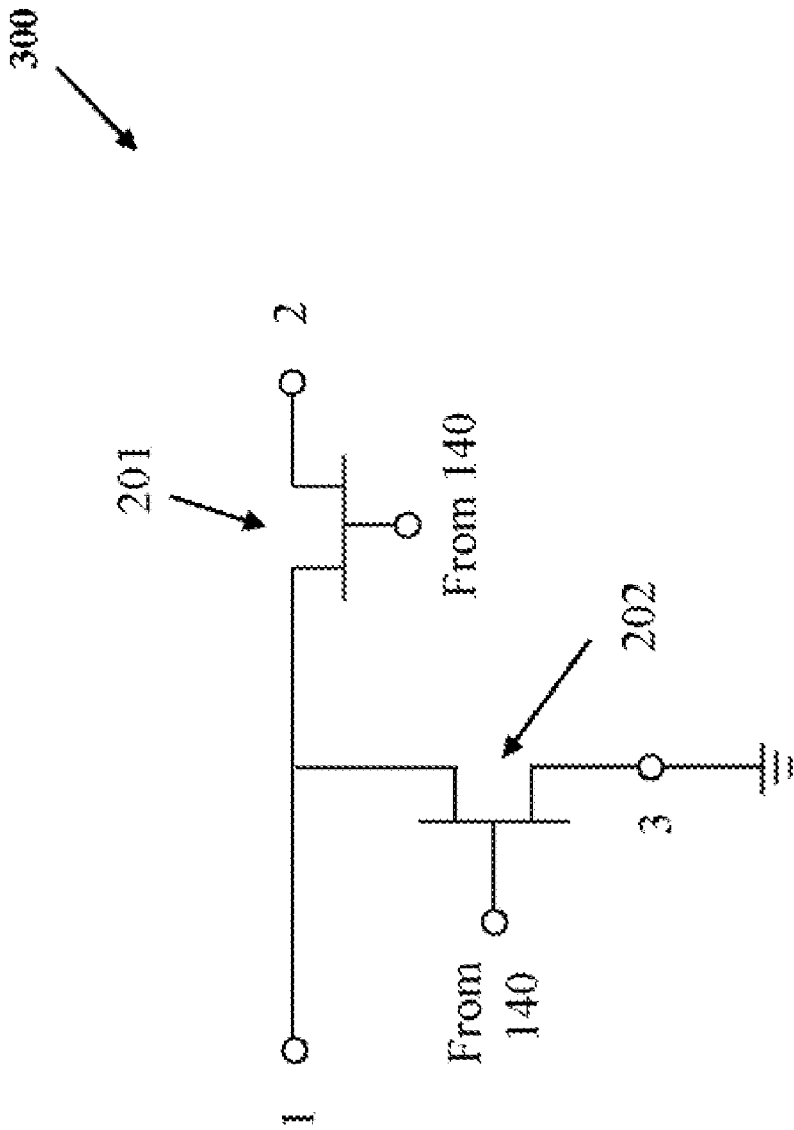


Figure 3

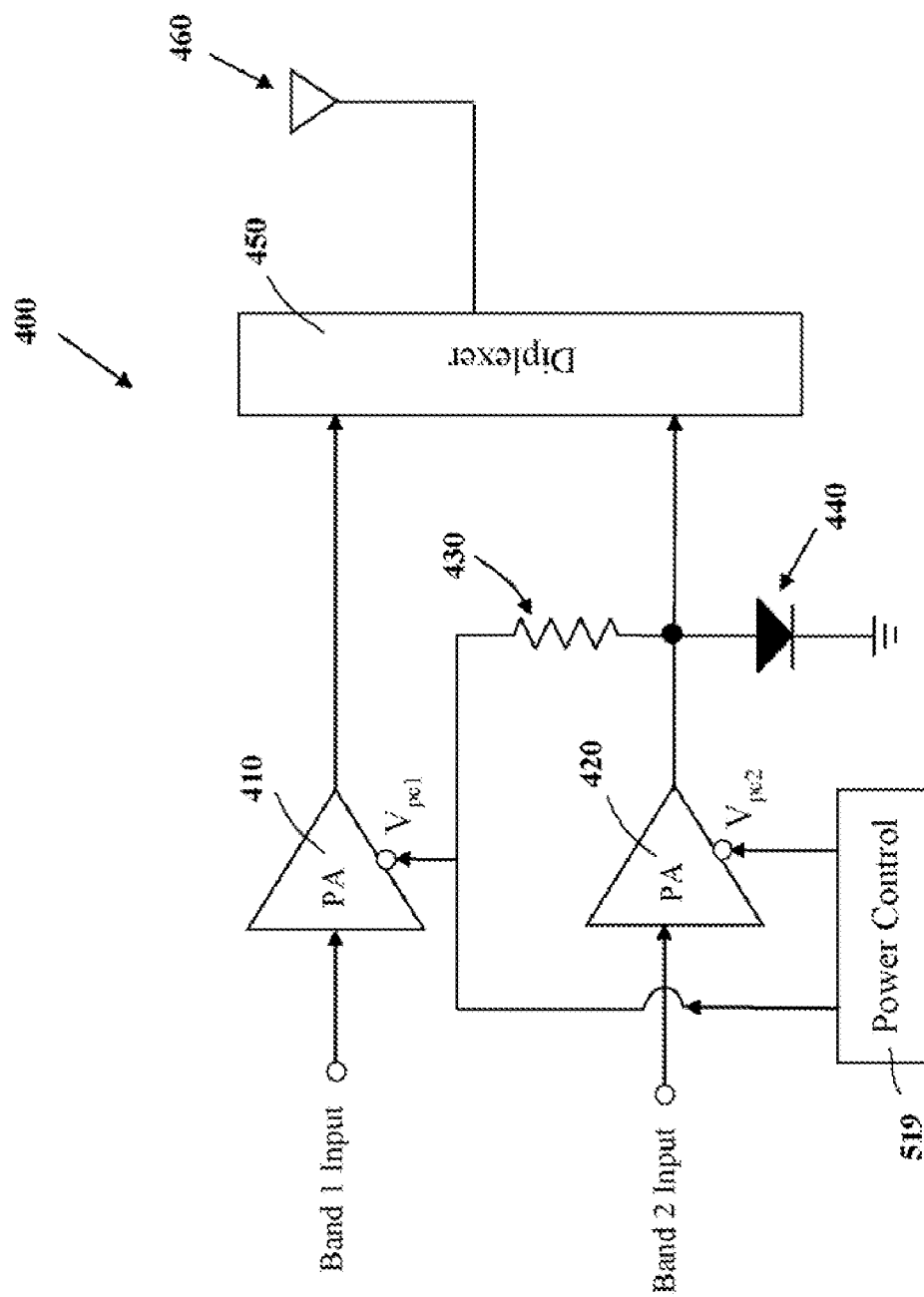


Figure 4

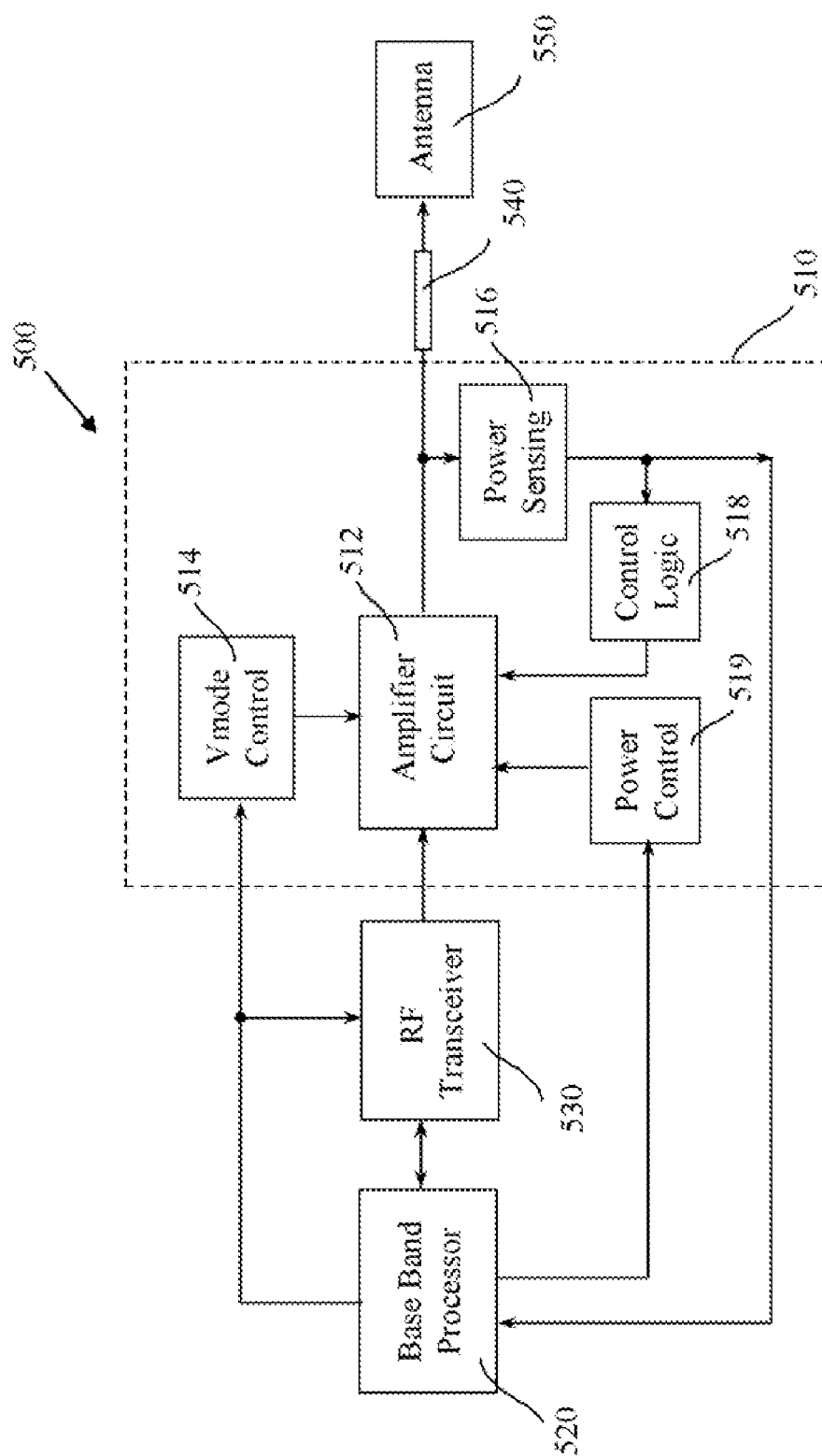


Figure 5

MULTI-BAND AMPLIFIER MODULE WITH HARMONIC SUPPRESSION

BACKGROUND

[0001] The present invention related to power amplifiers, and more particularly, to power amplifiers capable of communicating in two or more frequency bands.

[0002] Portable devices such as laptop personal computers, Personal Digital Assistant (PDA) and cellular phones with wireless communication capability are being developed in ever decreasing size for convenience of use. Correspondingly, the electrical components thereof must also decrease in size while still providing effective radio transmission performance. However, the substantially high transmission power associated with radio frequency (RF) communication increases the difficulty of miniaturization of the transmission components.

[0003] Power amplifier (PA) is a major component of a wireless communication device. A PA can be fabricated on a semiconductor integrated circuit (IC) chip to provide signal amplification with substantial power. The power amplifier chip can be interconnected with certain passive components such as inductors, capacitors, resistors, and transmission lines for operation controls and for providing impedance matching to the input and output RF signals.

[0004] Some wireless communication devices can communicate in more than one frequency band. For example, a wireless communication device may support the 802.11a standard at 5 GHz and 802.11b (and/or 802.11g) standard 2.4 to 2.5 GHz. For cost reduction and size constraints, it is desirable that both frequency bands utilize the same antenna in the wireless communication device. To achieve the desired levels of output power, separate output power amplifiers and transmission paths are needed to amplify and convey transmit data for each frequency band to separate inputs of a diplexer having and output coupled to a common antenna. The output power amplifiers tend to generate non-linear distortion so that certain amounts of harmonic energy are radiated at their outputs. This harmonic energy is particularly problematic given that the second harmonic of the low frequency band (e.g., approximately 4.8-5.0 GHz) is in the proximity range of the second 5 GHz band. Thus, it is difficult to filter the second harmonics of the low frequency band (at 2.4-2.5 GHz) in the transmission path of the high-frequency band at 5 GHz. Although pass filters may be employed for each transmission path to prevent undesired signal from an active transmission path from being directly conveyed to the diplexer, the second harmonic energy from the low-frequency band transmission path coupled or leaked into the high-frequency band transmission path is passed with very low loss. For example, any second harmonic energy of the low frequency signal coupled into the high-frequency band transmission path will also pass through the diplexer to the antenna causing the radio to fail necessary compliance harmonic specifications promulgated in the U.S. by the Federal Communications Commission (FCC) and internationally by the European Telecommunications Standards Institute (ETSI). Another attempt to control the second harmonic coupling (as described in US Patent Publication 20040127185) uses a trap circuit such as an LC circuit to attenuate the second harmonic energy at the higher frequency band.

[0005] A major disadvantage of the above described conventional techniques is that the circuit features intended for absorbing second harmonic energies can also attenuate the

signals in the higher frequency band. The problem is especially severe when the higher frequency band is within or overlaps with the doubling of the low-frequency band.

SUMMARY

[0006] In a general aspect, the present invention relates to an amplifier circuit that includes a first power amplifier that can produce a first amplified signal in response to a first input signal in a first frequency band; a second power amplifier that can produce a second amplified signal in response to a second input signal in a second frequency band, wherein a center frequency of the second frequency band is higher than the a center frequency of frequency band; a control circuit that can turn on or turn off the first power amplifier and turn on or turn off the second power amplifier; and a shunting circuit coupled to an output of the second power amplifier, wherein the shunting circuit can attenuate harmonic signals from the first frequency band under the control of the control circuit.

[0007] In another general aspect, the present invention relates to an amplifier circuit that includes a first power amplifier having a first power control terminal, wherein the first power amplifier can produce a first amplified signal in response to a first input signal in a first frequency band; a second power amplifier having a second power control terminal, wherein a center frequency of the second frequency band is higher than the a center frequency of frequency band, wherein the second input signal has a higher frequency than the first input signal; a control circuit that can send a first control signal to the first power control terminal of the first power amplifier to turn on or turn off the first power amplifier and to send a second control signal to the second power control terminal of the second power amplifier to turn on or turn off the second power amplifier; and a shunting circuit coupled to an output of the second power amplifier, wherein the shunting circuit can be activated by the first control signal to attenuate harmonic signals from the first power amplifier.

[0008] In yet another general aspect, the present invention relates to an integrated power amplifier module that includes a first power amplifier that can produce a first amplified signal in response to a first input signal in a first frequency band; a second power amplifier that can produce a second amplified signal in response to a second input signal in a second frequency band, wherein a center frequency of the second frequency band is higher than the a center frequency of frequency band; a control circuit that can turn on or turn off the first power amplifier and configured to turn on or turn off the second power amplifier; and a shunting circuit coupled to an output of the second power amplifier, wherein the shunting circuit can attenuate harmonic signals of the first frequency band under the control of the control circuit, wherein the first power amplifier, the second power amplifier, the control circuit, and the shunting circuit are constructed on a single semiconductor die.

[0009] Implementations of the system may include one or more of the following. The shunting circuit can attenuate harmonic signals of the first frequency band when the first power amplifier is turned on by the control circuit. The amplifier circuit can further include a diplexer configured to receive the first amplified signal from the first power amplifier and the second amplified signal from the second power amplifier, wherein the diplexer can send at least one of the first amplified signal and the second amplified signal to an antenna. The shunting circuit can bypass the output of the second power amplifier to ground when the second power amplifier is

turned off by the control circuit. The shunting circuit can pass the second amplified signal to the diplexer when the second power amplifier is turned on by the control circuit. The amplifier circuit can further include a trap circuit coupled between the shunting circuit and the ground, wherein the trap circuit is configured to attenuate a harmonic signal from the first frequency band. The shunting circuit can include a first transistor coupled between an output of the second power amplifier and an output terminal; and a second transistor coupled between the output of the second power amplifier and the ground, wherein the first transistor and the second transistor are controlled by the control circuit, wherein the first transistor and the second transistor are configured to attenuate harmonics from the first frequency band when the first power amplifier is turned on and to pass the second amplified signal to the output terminal when the second power amplifier is turned on by the control circuit. The amplifier circuit can further include a diplexer configured to receive the first amplified signal from the first power amplifier and coupled to the output terminal, wherein the diplexer is configured to send at least one of the first amplified signal and the second amplified signal to an antenna. The first power amplifier can include a first power control terminal configured to receive a first control signal from the control circuit to turn on or turn off the first power amplifier and the second power amplifier comprises a second power control terminal configured to receive a second control signal from the control circuit to turn on or turn off the second power amplifier. The shunting circuit can include a resistor connected between the power control terminal of the first power amplifier and an output of the second power amplifier; and a PIN diode coupled between the ground and the output of the second power amplifier, wherein the control circuit is configured to send the first control signal to turn on the first power amplifier and to activate the PIN diode to attenuate harmonic signals from the first power amplifier. The second frequency band can overlap with at least a portion of a harmonic band from the first frequency band.

[0010] Embodiments may include one or more of the following advantages. The disclosed amplifier circuits can provide high-linearity radio frequency power amplification for dual or multiple frequency bands with significantly reduced noise and unwanted signal oscillations. The disclosed amplifier circuits can effectively suppress harmonic signals from low-frequency band transmission path without attenuating signals in the higher frequency band.

[0011] The disclosed amplifier circuits are especially advantageous over some conventional power amplifiers when the higher frequency band is within or overlaps with the harmonic signals of the low-frequency band in a wireless device. For example, the disclosed amplifier circuits can be applied to wireless communication devices that support multiple standards such as WiMax and WiFi. The disclosed amplifier circuits can suppress the second harmonics from a low-frequency band operating at 2.3-2.7 GHz without attenuating the signals in a high-frequency band operating at 5 GHz even if 5 GHz overlaps with the second harmonic frequency (4.6-5.4 GHz) of the low frequency band, the frequency range of harmonic signals from the low frequency band transmission path.

[0012] Another advantage of the disclosed amplifier circuits is that the components involved are highly integrated. One or more of the power amplifiers, the components for suppressing harmonics, the control circuit, and the diplexer

can be integrated in a single IC chip. The disclosed power amplifier circuits can be more compact compared to some prior art implementations.

BRIEF DESCRIPTION OF THE DRAWINGS

[0013] The following drawings, which are incorporated in and from a part of the specification, illustrate embodiments of the present specification and, together with the description, serve to explain the principles of the specification.

[0014] FIG. 1 is a schematic diagram for a power amplifier circuit having harmonic suppression.

[0015] FIG. 2 is a schematic diagram for another power amplifier circuit having harmonic suppression.

[0016] FIG. 3 is a schematic diagram for a shunting circuit compatible with the power amplifier circuits shown in FIG. 1 and FIG. 2.

[0017] FIG. 4 illustrates an implementation of a power amplifier circuit having harmonic suppression.

[0018] FIG. 5 illustrates an exemplified implementation of an amplifier circuit having harmonic suppression in a wireless communication device in accordance with the present specification.

DETAILED DESCRIPTION

[0019] A power amplifier circuit 100, referring to FIG. 1, includes a power amplifier 110 for amplifying signals in a low frequency band, Band 1, and a power amplifier 120 for amplifying signals in a high frequency band, Band 2. Each of the Band 1 and Band 2 can be characterized by a center frequency. The center frequency of Band 2 is higher than the center frequency of Band 1. The two frequency bands can support different standards such as WiFi, WiMax, and 802.11b (and/or 802.11g). For example, Band 1 can operate at 2.3-2.7 GHz. Band 2 can operate at about 5 GHz. The second harmonic band for Band 1 is thus at 4.6-5.4 GHz, which may overlap with the frequency band of Band 2.

[0020] In the present specification, the term 'harmonic band' refers to the frequency band for the harmonic signals from a lower frequency band. The signal path for each frequency band can be referred to as a transmission path. A first transmission path refers to the amplification path for Band 1 and a second transmission path refers to the amplification path for Band 2.

[0021] The power amplifier circuit 100 also includes a shunting circuit 130 and a control circuit 140. The control circuit 140 can control power input to the power amplifiers 110 and 120. The control circuit 140, as described in more detail below, can also control the shunting operations of the shunting circuit 130. A diplexer can combine the amplified signals from the power amplifiers 110 and 120 and supply the amplified signals to an antenna 160.

[0022] The control circuit 140 can send control signals to turn on or turn off the power supplies to the power amplifiers 110 and 120. For example, the control circuit 140 can turn on power amplifier 110 and turn off the power amplifier 120 to allow signals in Band 1 to be amplified, then to pass through the diplexer 150 and to be transmitted by the antenna 160. The diplexer 150 includes a low-pass filter or a band-pass filter for the low-frequency band transmission path and a high-pass filter or a band-pass filter for the high-frequency band transmission path. The control circuit 140 can also turn on power amplifier 120 and turn off the power amplifier 110 to allow signals in Band 2 to be amplified, then to pass through the

diplexer **150** and to be transmitted by the antenna **160**. The power control signals from the control circuit **140** can be respectively sent to the power-control Vpc terminals in the power amplifiers **110** and **120**. In one example, a high voltage at the power-control Vpc terminal can turn on the power amplifier **110** or **120**. A low voltage at the power-control Vpc terminal can turn off the power amplifier **110** or **120**.

[0023] The shunting circuit **130** can be logically represented by a switch having three terminals **1**, **2**, and **3**. Terminal **1** is connected to output of the power amplifier **120**. Terminal **2** is connected to the diplexer **150**. Terminal **3** is connected to the ground. The control circuit **140** can control the shunting circuit **130** to connect terminal **1** to either terminal **2** or terminal **3**. The shunting circuit **130** is deactivated when terminal **1** is connected to terminal **2**. The shunting circuit **130** is activated when terminal **1** is connected to terminal **3** (e.g. ground for the amplifier circuit in FIG. 1).

[0024] When the power amplifier **110** is turned on, terminal **1** is connected to terminal **3** under the control of the control circuit **140**. The output of the power amplifier **120** is disconnected from the diplexer **150** and shunted to the ground. Harmonic signals originated from the low-frequency band transmission path may be coupled or leaked to the high-frequency band transmission path because the transmission circuits for the two transmission paths are typically constructed in vicinity in a integrated circuit on a same substrate. Without proper attenuation, the harmonic signals from the low-frequency band transmission path can pass through the high-pass filter or the band filter in the diplexer **150**, which leads to non-linearity in the output RF signal. Harmonic signals from the low-frequency band transmission path are thus bypassed to the ground and the open circuit at the shunting **130** prevents the harmonic signals from reaching the diplexer **150**. The quality of the output signal to the antenna is therefore much enhanced.

[0025] When the amplifier circuit **100** amplifies signals in Band **2**, the power amplifier **120** is turned on; the power amplifier **110** is turned off. Terminal **1** in the shunting circuit **130** is controlled by the control circuit **140** to connect to terminal **2**. The amplified signals from the power amplifier **120** in Band **2** can propagate to the diplexer **150** and then be transmitted by the antenna **160**.

[0026] The logic states of the amplifier circuits **100**, **200** and the shunting circuit **130** are illustrated in Table 1.

TABLE 1

Logic States for the power amplifiers and the shunting circuit			
Transmission Mode	PA in Band 1	PA in Band 2	Shunting Circuit
Band 1	ON	OFF	ACTIVATED
Band 2	OFF	ON	DEACTIVATED

[0027] One advantage for the amplifier circuits **100** is that the associated shunting circuit **130** does not attenuate high-frequency signals when the power amplifier **110** is off and the power amplifier **120** is on. This feature overcomes a major shortcoming in some conventional amplifier circuit where signals in the high frequency band may be indiscriminately attenuated even when the high frequency signals are to be amplified. The described advantage of the disclosed amplifier circuit is especially important when the Band **2** operates at or around twice or other multiple of the frequency of Band **1**. For example, Band **1** can operate in a frequency range of 2.3-2.7

GHz and Band **2** can operate at about 5 GHz. The high frequency signals at about 5 GHz is not attenuated when the power amplifier **120** is on (as is the case in some conventional systems). This advantageous feature assures gain uniformity across the high frequency band in the disclosed amplifier circuit.

[0028] In another implementation, referring to FIG. 2, an amplifier circuit **200**, includes an additional trap circuit **170** between the terminal **3** in the shunting circuit **130** and the ground. The trap circuit **170** can be implemented, for example, by a resonant circuit such as an LC circuit that is designed to have low impedance at the frequencies of the harmonic signals from the low-frequency band transmission path. For example, if Band **1** operates at 2.3-2.7 GHz, the resonance frequency from the resonant circuit can be designed to be at around 4.6-5.4 GHz. The addition of the trap circuit **170**, although optional, can further absorb the harmonic signals from the low-frequency band transmission path.

[0029] The shunting circuit **130** can be implemented by circuit components such as PIN diodes. High Electron Mobility Transistors (HEMT), Metal-Semiconductor Field Effect Transistors (MESFET), and Complementary metal-oxide-semiconductor (CMOS) circuits, etc. FIG. 3 shows a schematic diagram of a shunting circuit **300** that is compatible with the shunting circuit **130** in the power amplifier circuits **100** and **200**. Tire shunting circuit **300** includes a transistor **201** connected between the terminal **1** and terminal **2** and a transistor **202** connected between the terminal **1** and terminal **3** (ground). The gates of the transistor **201** and the transistor **202** can receive control signals from the control circuit **140**. For example, the shunting circuit **300** is activated when the transistor **202** is turned on and the transistor **201** is turned off by the control circuit **140**. The shunting circuit **300** can be deactivated when the transistor **201** is turned on and the transistor **202** is turned off by the control circuit **140**.

[0030] FIG. 4 illustrates another implementation of a power amplifier circuit having harmonic suppression. A power amplifier circuit **400** includes a power amplifier **410** for amplifying signals in a low frequency band, Band **1**, and a power amplifier **420** for amplifying signals in a high frequency band, Band **2**. The two frequency bands can support different standards such as WiFi, WiMax, and 802.11b (and/or 802.11g). For example, Band **1** can operate at 2.3-2.7 GHz, Band **2** can operate at about 5 GHz. The second harmonic band for Band **1** is thus at 4.6-5.4 GHz, which may overlap with the Band **2**.

[0031] The power control terminal Vpc1 of the power amplifier **410** can receive a control signal from a power control **519** (shown in FIG. 5 as described below). The power control terminal Vpc2 of the power amplifier **420** can also receive a control signal from a power control **519** (shown in FIG. 5 as described below). For example the power amplifiers **410**, **420** can be turned on when high-voltage signals are respectively received at the power control terminals Vpc1 and Vpc2.

[0032] The power amplifier circuit **400** also includes a shunting circuit that includes a resistor **430** and a PIN diode **440** that is connected to the ground. A PIN diode refers a diode with a wide, un-doped intrinsic semiconductor region between p-type semiconductor and n-type semiconductor regions of the diode. A PIN diode obeys the standard diode equation only for slow-varying signals. At higher frequencies, the diode looks like an almost perfect (very linear, even

for large signals) resistor. The high-frequency resistance is inversely proportional to the DC bias current through the diode. A PIN diode, suitably biased, therefore can act as a variable resistor. This high-frequency resistance may vary over a wide range. The PIN diode **440** can thus effectively attenuate high frequency harmonic signals when a high voltage signal is applied to the Vpc1 terminal and the resistor **430**.

[0033] In one implementation, turn-on voltage for Vpc1 can be 2.8 V. The resistor **430** can have a resistance of 1K Ohm, which can drive a current of about 1 mA to the PIN diode **440**. This current can activate the PIN diode to shunt die harmonic signals from the low-frequency band transmission path at the output of the power amplifier **420**. Furthermore, the PIN diode **440** can be implemented in a very compact area. The compact implementation of the shunting circuit allows the power amplifier circuit **400** to be highly integrated and implemented in an integrated circuit on a semiconductor substrate.

[0034] The power amplifier circuit **400** can operate as follows. When signals from Band 1 are to be amplified, Vpc1 is controlled at high voltage and Vpc2 is controlled at low voltage. The power amplifier **410** is turned on to amplify signals in Band 1. The power amplifier **410** is turned off. The high voltage at Vpc1 raises the bias voltage for the resistor **430** and across the PIN diode **440** to make the PIN diode **440** conductive. The PIN diode can effectively shunts harmonic signals from the low-frequency band transmission path to the ground. When signals from Band 2 are to be amplified, Vpc1 is controlled at low voltage and Vpc2 is controlled at high voltage. The power amplifier **410** is turned off. The power amplifier **420** is turned on to amplify signals in Band 2. The low bias voltage at the Vpc1 makes the PIN diode **440** non-conductive for RF signals. The amplified signals from the power amplifier **420** can pass to the diplexer **450** and then be transmitted by antenna **460**.

[0035] FIG. 5 illustrates an exemplary application of an amplifier circuit **512** in a wireless communication device **500**. The wireless communication device **500** can for example be a PDA, a WiFi device, a WiMax device, or a cellular phone. The amplifier circuit **512** can be implemented by the amplifier circuit **100**, **300**, or **400** as previously described. The wireless communication device **500** can include a base band processor core **520**, an RF transceiver **530**, a power amplifier module **510** capable of operating at multiple frequency bands, and a 50-ohm impedance transmission line or micro strip **540** and an antenna **550**. The power amplifier module **510** can include the amplifier circuit **512**, a Vmode control circuit **514**, a power sensing circuit **516**, a control logic circuit **518**, and a power control circuit **519**. The control circuits **130** in the amplifier circuits **100** and **200** can include at least portions of the power control **519** and the control logic **518**. The power control circuit **519** can also provide control signals for the power control terminals Vpc1 and Vpc2 of the power amplifiers **410**, **420** in the power amplifier circuit **400**. In some embodiments, the power amplifier module **510** is fabricated on an integrated circuit (IC) module that can be implemented on a single semiconductor chip.

[0036] The amplifier circuit **512** can include a biasing circuit for providing biasing signals to the one or more power amplifiers (e.g. **110**, **120**, **410**, and **420**) and power drivers in the amplifier circuit **512**. The biasing circuit can control the bias of the power amplifiers and the power drivers in response to a control signal from the control circuit **140** (that can include at least portions of the control logic **518** and the power

control **519**). The control circuit **140** can produce the control signals to the biasing circuit based on a power sensing signal received from the power sensing circuit **516**.

[0037] The amplifier circuit **512** can also include impedance matching circuits for input and output signals. Details of impedance matching circuits are described commonly assigned U.S. patent application Ser. No. 10/041,863, filed on Oct. 22, 2001, titled "Multilayer RF Amplifier Module", by Wang, et al., the content of which is incorporated by reference.

[0038] The base band processor **520** can generate and process digitally modulated signals. The frequency is up-converted by the RF transceiver **530** to a RF signal suitable for transmission. The RF signal is amplified by the PA module **510** that produces amplified RF signal for transmission by the antenna **550**. The PA module **510** can be turned ON/OFF by the power control signal produced by the power control circuit **519**.

[0039] In some embodiments, the amplifier circuit **512** can be controlled by an open loop by the base band processor **520** via Vmode control circuit **514**. The Vmode control circuit **514** can produce a Vmode control signal to control and internal settings of the biasing circuits under the control of (the base band processor **520**). The base band processor **520** has the knowledge of the digital signal modulation type and the linear output requirement. For example, when the device is transmitting at high power, the Vmode control signal can control the biasing circuit to activate the main power amplifier. When the device is transmitting at low power, the Vmode control signal can control the biasing circuit to activate the auxiliary power amplifier. As a result, power consumption and output distortion can be minimized.

[0040] To provide excellent output linearity, a power amplifier must maintain a constant gain (which is defined as the ratio of the output signal power level to the input signal power level) over a wide output range. However, the power amplifier can be driven close to saturation at high output power level, which makes it difficult to maintain a constant gain. The quality of digital communication, especially the quality degrades at high output power level, can commonly be measured by Error Vector Magnitude (EVM), Bit Error Rate (BER), Packet Error Rate (PER), and Adjacent Channel Power Ratio (ACPR).

[0041] In some embodiments, the amplifier circuit **512** can be controlled by a close loop by the power sensing circuit **516**. The output linearity can be improved by a feedback control based on the sensing of the output power level. The power sensing circuit **516** can measure the power of the output RF signal and send a power sensing signal to the base band processor **520**. The base band processor **520** can set the transmission power level by varying the input signal to the RF transceiver **530** and thus to the PA module **510** in accordance to the power sensing signal received by the power sensing circuit **516**. The control logic circuit **518** can process the power-sensing signal from the power sensing circuit **516** and compute a quality or a magnitude of the output signal. A power-sensing control signal is then generated to control the biasing circuit in response to the quality, or the magnitude, or a combination thereof of the output signal. Other details of the power sensor circuit are disclosed in commonly assigned U.S. patent application Ser. No. 10/385,059 titled "Accurate Power Sensing Circuit for Power Amplifiers" Mar. 9, 2003, by Ichitsubo et al., the disclosures of which related application are incorporated herein by reference.

[0042] The control logic circuit **518** can receive and process the power-sensing control signal, and output a processed power-sensing control signal to control the amplifier circuit **512**. The processed power-sensing control signal can be a function of the quality and/or the magnitude of the amplified radio frequency signals from the amplifier circuit **512**. The control logic circuit **518** can improve output linearity of the amplifier circuit **512** by adjusting the bias of the biasing circuits in accordance to the actual output power measured by the power sensing circuit **516**. It can reduce gain saturation and maintain a more constant gain, which can improve the output linearity in a wide power range. Furthermore, the quality of digital communication can also be improved by an external controller that can adjust the amplitude of the input. RF signal based the known relationship between digital communication quality and output power level.

[0043] In some embodiments, the PA module **510** can be fabricated on an integrated circuit (IC) module that can be implemented on a single semiconductor chip (or die). The PA module **510** can also be implemented as an integrated circuit on a common semiconductor substrate which can be a multi-layer printed circuit board (PCB), lead frame, lower-temperature co-fired ceramics (LTCC), or other suitable electronic materials. The substrate includes metal Pins adapted to receive connecting terminals of integrated circuits including the first stage power amplifier, the main and the auxiliary power amplifiers, the biasing circuit, power sensing circuit, Vmode control circuit, and optional control logic circuit. The amplifier IC chip can include electrically conductive layers and patches for proper grounding and cooling of the PA module **510**.

[0044] The PA module provides a unitary or common component which may be conveniently assembled in a RF transmission device, with correspondingly simplified assembly, compact sizes, and enhanced RF amplification performance. In accordance with the present invention, the term "module" refers to such a unitary device for wireless communications, comprising integrated power amplifiers and other circuitry and auxiliary electronic components. The disclosed PA module can be applied to a wide range wireless communication devices such as cellular phone, mobile computers, and handheld wireless digital devices. The PA module has a miniature size of a few millimeters. Other details about power amplifier modules are disclosed in commonly assigned U.S. patent application Ser. No. 11/486,465 titled "Thermally distributed integrated power amplifier module", filed Jul. 16, 2006, by Ichitsubo et al., the disclosures of which related application are incorporated herein by reference.

[0045] It is understood the disclosed amplifier circuits can be compatible with other variations without deviating from the spirit of the present application. For example, the shunting circuit can be implemented in many different tones and with different components to provide similar functions. The disclosed amplifier circuit can amplify signals in more than two frequency bands. The disclosed circuit can be applied to attenuate harmonics at two (i.e. second harmonics), three, or other multiple of a low frequency signal in one of the transmission paths in the disclosed amplifier circuit. The disclosed amplifier circuit can also include several stages in each power amplifier. An amplifier driver can also be included before a power amplifier.

[0046] The disclosed amplifier circuits are suitable to applications in various wireless data and voice communications standards and protocols, including Orthogonal Frequency-

Division Multiplexing (OFDM), Orthogonal Frequency-Division Multiplexing Access (OFDMA), Code Division Multiple Access (CDMA), Wideband Code Division Multiple Access (WCDMA), High-Speed Downlink Packet Access (HSDPA), High-Speed Packet Access (HSPA), Ultra Mobile Broadband (UMB), Long Term Evolution (LTE), WiMax, WiBro, WiFi, WLAN, and others. The disclosed amplifier circuits are also suitable for high frequency operations by utilizing Gallium Arsenide Heterojunction Bipolar Transistors (GaAs HBT).

What is claimed is;

1. An amplifier circuit, comprising:

- a first power amplifier configured to produce a first amplified signal in response to a first input signal in a first frequency band;
- a second power amplifier configured to produce a second amplified signal in response to a second input signal in a second frequency band, wherein a center frequency of the second frequency band is higher than the a center frequency of frequency band;
- a control circuit configured to turn on or turn off the first power amplifier and configured to turn on or turn off the second power amplifier; and
- a shunting circuit coupled to an output of the second power amplifier, wherein the shunting circuit is configured to attenuate harmonic signals from the first frequency band under the control of the control circuit.

2. The amplifier circuit of claim 1, wherein the shunting circuit is configured to attenuate harmonic signals of the first frequency band when the first power amplifier is turned on by the control circuit.

3. The amplifier circuit of claim 1, further comprising a diplexer configured to receive the first amplified signal from the first power amplifier and the second amplified signal from the second power amplifier, wherein the diplexer is configured to send at least one of the first amplified signal and the second amplified signal to an antenna.

4. The amplifier circuit of claim 3, wherein the shunting circuit is configured to bypass the output of the second, power amplifier to ground when the second power amplifier is turned off by the control circuit.

5. The amplifier circuit of claim 3, wherein the shunting circuit is configured to pass the second amplified signal to the diplexer when the second power amplifier is turned on by the control circuit.

6. The amplifier circuit of claim 1, further comprising a trap circuit coupled between the shunting circuit and the ground, wherein the trap circuit is configured to attenuate a harmonic signal from the first frequency band.

7. The amplifier circuit of claim 1, wherein the shunting circuit comprises:

- a first, transistor coupled between an output of the second power amplifier and an output terminal; and
- a second transistor coupled between the output of the second power amplifier and the ground, wherein the first transistor and the second transistor are controlled by the control circuit, wherein the first transistor and the second transistor are configured to attenuate harmonics from the first frequency band when the first power amplifier is turned on and to pass the second amplified signal to the output terminal when the second power amplifier is turned on by the control circuit.

8. The amplifier circuit of claim 7, further comprising a diplexer configured to receive the first amplified signal from

the first power amplifier and coupled to the output terminal, wherein the diplexer is configured to send at least one of the first amplified signal and the second amplified signal to an antenna.

9. The amplifier circuit of claim 1, wherein the first power amplifier comprises a first power control terminal configured to receive a first control signal from the control circuit to turn on or turn off the first power amplifier and the second power amplifier comprises a second power control terminal configured to receive a second control signal from the control circuit to trim on or trim off the second power amplifier.

10. The amplifier circuit of claim 9, wherein the shunting circuit comprises:

- a resistor connected between the power control terminal of the first power amplifier and an output of the second power amplifier; and

- a PIN diode coupled between the ground and the output of the second power amplifier, wherein the control circuit is configured to send the first control signal to turn on the first power amplifier and to activate the PIN diode to attenuate harmonic signals from the first power amplifier.

11. The amplifier circuit of claim 1, wherein the second frequency band overlaps with at least a portion of a harmonic band from the first frequency band.

12. An amplifier circuit, comprising:

- a first power amplifier having a first power control terminal, wherein the first power amplifier is configured to produce a first amplified signal in response to a first input signal in a first frequency band;

- a second power amplifier having a second power control terminal, wherein the second power amplifier is configured to produce a second amplified signal in response to a second input signal in a second frequency band, wherein a center frequency of the second frequency band is higher than a center frequency of frequency band;

- a control circuit configured to send a first control signal to the first power control terminal of the first power amplifier to turn on or turn off the first power amplifier and to send a second control signal to the second power control terminal of the second power amplifier to turn on or turn off the second power amplifier; and

- a shunting circuit coupled to an output of the second power amplifier, wherein the shunting circuit is configured to be activated by the first control signal to attenuate harmonic signals from the first power amplifier.

13. The amplifier circuit of claim 12, wherein the shunting circuit is activated to attenuate harmonic signals from the first power amplifier when the first control signal turns on the first power amplifier.

14. The amplifier circuit of claim 12, further comprising a diplexer configured to receive the first amplified signal from the first power amplifier and the second amplified signal from the second power amplifier, wherein the diplexer is configured to send at least one of the first amplified signal and the second amplified signal to an antenna.

15. The amplifier circuit of claim 14, wherein the shunting circuit is configured to bypass the output of the second power amplifier to ground when the second power amplifier is turned off by the control circuit, and wherein the shunting circuit is configured to pass the second amplified signal to the diplexer when the second power amplifier is turned on by the control circuit.

16. The amplifier circuit of claim 12, wherein the shunting circuit comprises:

- a resistor connected between the first power control terminal and an output of the second power amplifier; and
- a PIN diode coupled between the ground and the output of the second power amplifier.

17. The amplifier circuit of claim 16, wherein the control circuit is configured to send the first control signal to turn on the first power amplifier and to activate the PIN diode to attenuate harmonic signals from the first frequency band.

18. An integrated power amplifier module, comprising:

- a first power amplifier configured to produce a first amplified signal in response to a first input signal in a first frequency band;

- a second power amplifier configured to produce a second amplified signal in response to a second input signal in a second frequency band, wherein a center frequency of the second frequency band is higher than the a center frequency of frequency band;

- a control circuit configured to turn on or turn off the first power amplifier and configured to turn on or turn off the second power amplifier; and

- a shunting circuit coupled to an output of the second power amplifier, wherein the shunting circuit is configured to attenuate harmonic signals of the first frequency band under the control of the control circuit, wherein the first power amplifier, the second power amplifier, the control circuit, and the shunting circuit are constructed on a single semiconductor die.

19. The integrated linear power amplifier module of claim 18, further comprising a power sensing circuit coupled to the control circuit, wherein the power sensing circuit is configured to produce a power sensing signal in response to the power of at least one of the first amplified signal or the second amplifier signal.

20. The integrated linear power amplifier module of claim 18, further comprising a biasing circuit configured to control the bias of the first power amplifier and the second power amplifier, wherein a biasing circuit is coupled to the control circuit and is configured to control the bias of the first power amplifier and the second power amplifier in response to the power sensing signal.

21. The integrated linear power amplifier module of claim 18, further comprising:

- a power control circuit configured to control the power supplied to the amplifier circuit in response to a first external signal; and

- a Vmode control circuit configured to control the biasing mode of the biasing circuit in the amplifier circuit in response to a second external signal.

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